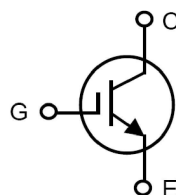


High Voltage XPT™ IGBT

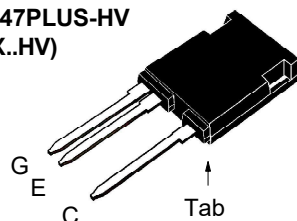
IXYX40N250CHV

$V_{CES} = 2500V$
 $I_{C110} = 40A$
 $V_{CE(sat)} \leq 4.0V$
 $t_{fi(typ)} = 134ns$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	2500	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	2500	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	154	A
I_{C110}	$T_C = 110^\circ C$	40	A
I_{CM}	$T_C = 25^\circ C$, 1ms	370	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 80$ 1500	A V
P_C	$T_C = 25^\circ C$	1500	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ C$
F_C	Mounting Force	20..120/4.5..27	N/lb
Weight		6	g

TO-247PLUS-HV
(IXYX..HV)



G = Gate E = Emitter
 C = Collector Tab = Collector

Features

- High Voltage Package
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- UPS
- Motor Drives
- SMPS
- PFC Circuits
- High Frequency Power Inverters

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			15 μA 4 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 40A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		3.2 4.4	V V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 40\text{A}, V_{CE} = 10\text{V}$, Note 1	24	42	S
R_{Gi}	Gate Input Resistance		2.0	Ω
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		5470	pF
C_{oes}			204	pF
C_{res}			74	pF
$Q_{g(on)}$	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		270	nC
Q_{ge}			28	nC
Q_{gc}			110	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		21	ns
t_{ri}			22	ns
E_{on}			11.7	mJ
$t_{d(off)}$			200	ns
t_{fi}			134	ns
E_{off}			6.9	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 40\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		21	ns
t_{ri}			22	ns
E_{on}			14.7	mJ
$t_{d(off)}$			255	ns
t_{fi}			250	ns
E_{off}			11.5	mJ
R_{thJC}				0.10 $^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (Clamp), T_J or R_G .

Littelfuse reserves the right to change limits, test conditions, and dimensions.

LF MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

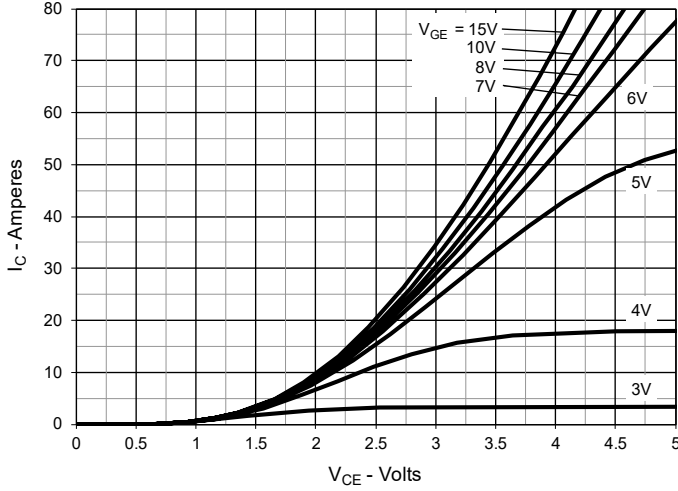
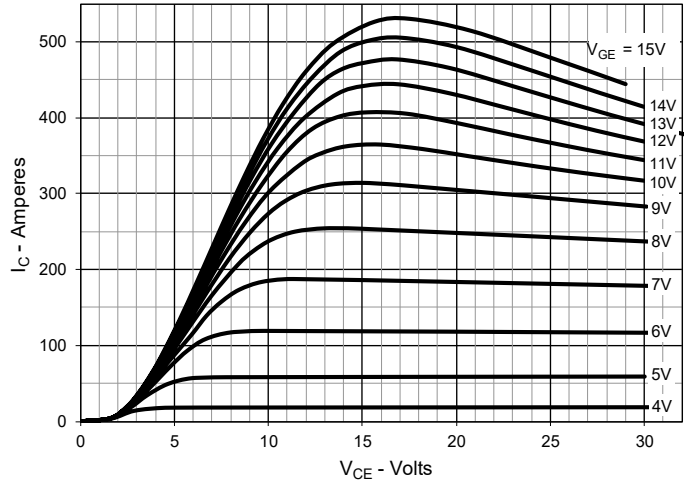
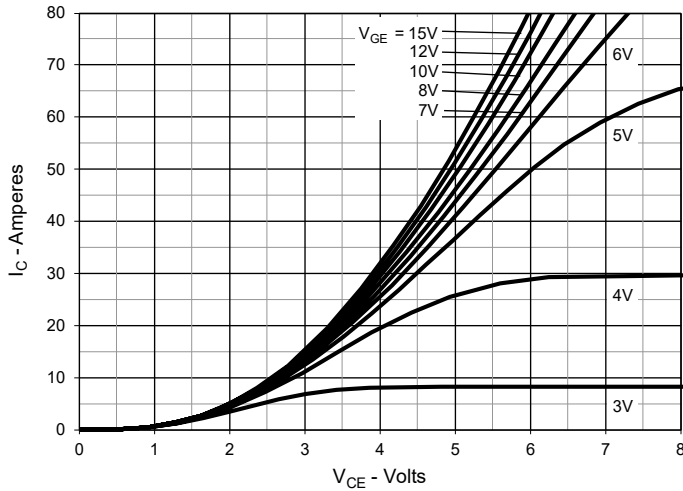
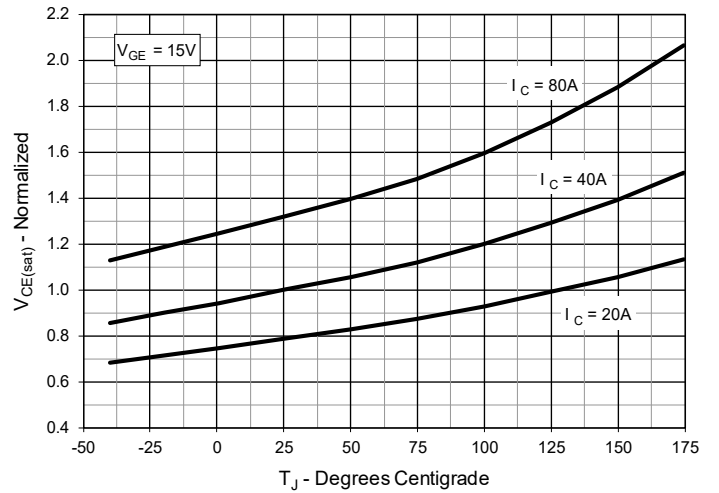
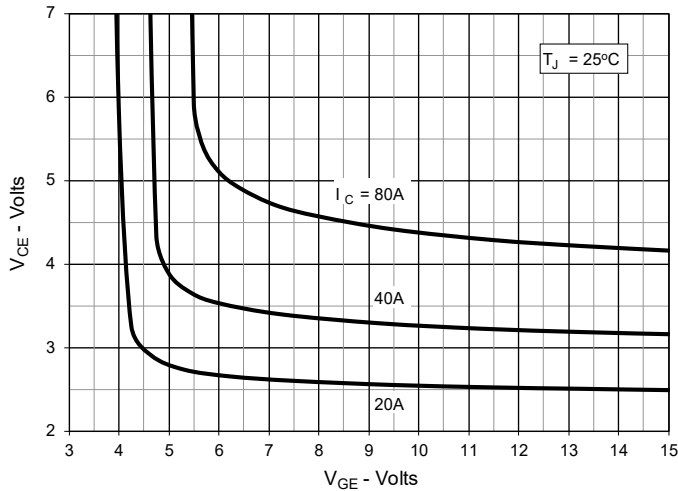
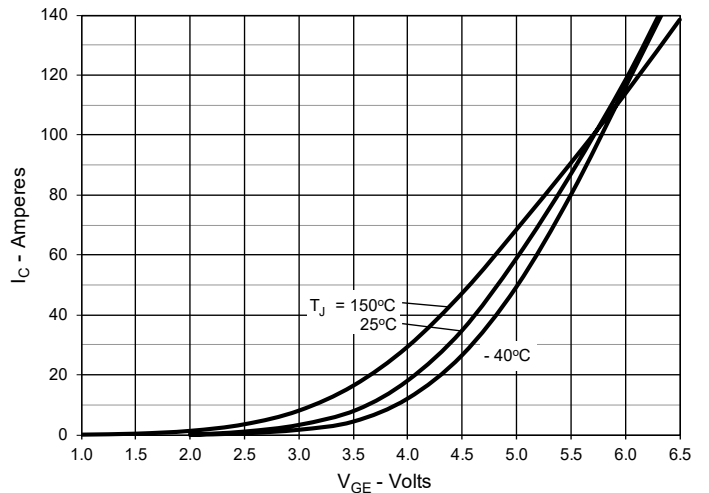
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

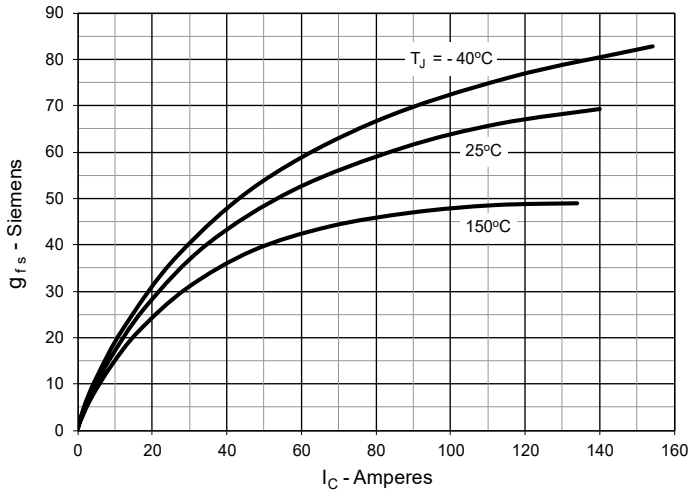


Fig. 8. Gate Charge

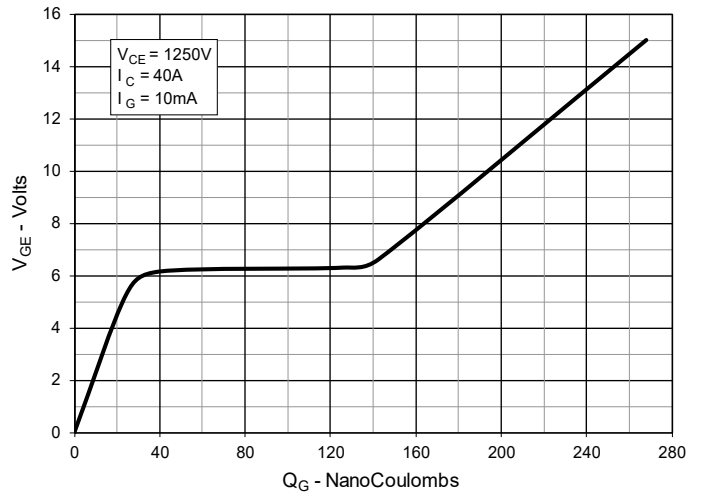


Fig. 9. Capacitance

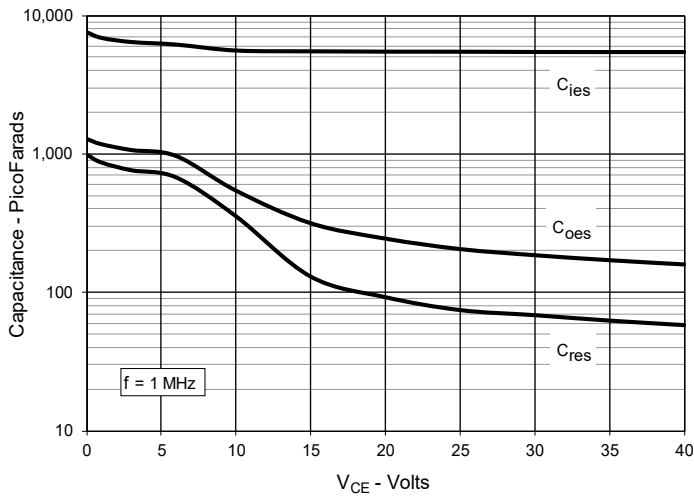


Fig. 10. Reverse-Bias Safe Operating Area

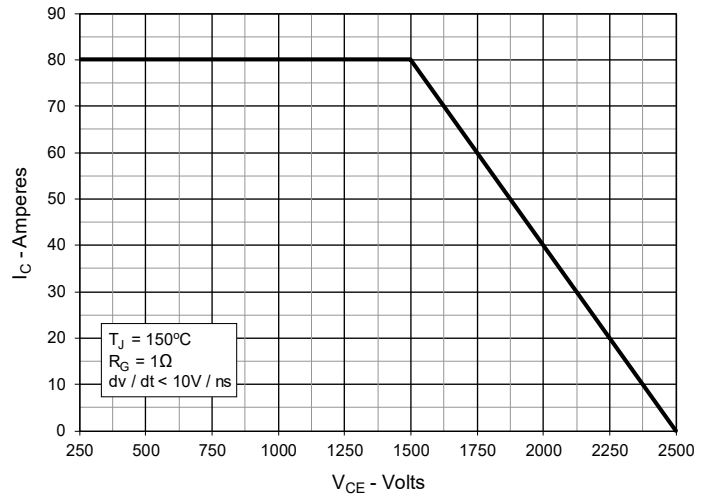


Fig. 11. Maximum Transient Thermal Impedance

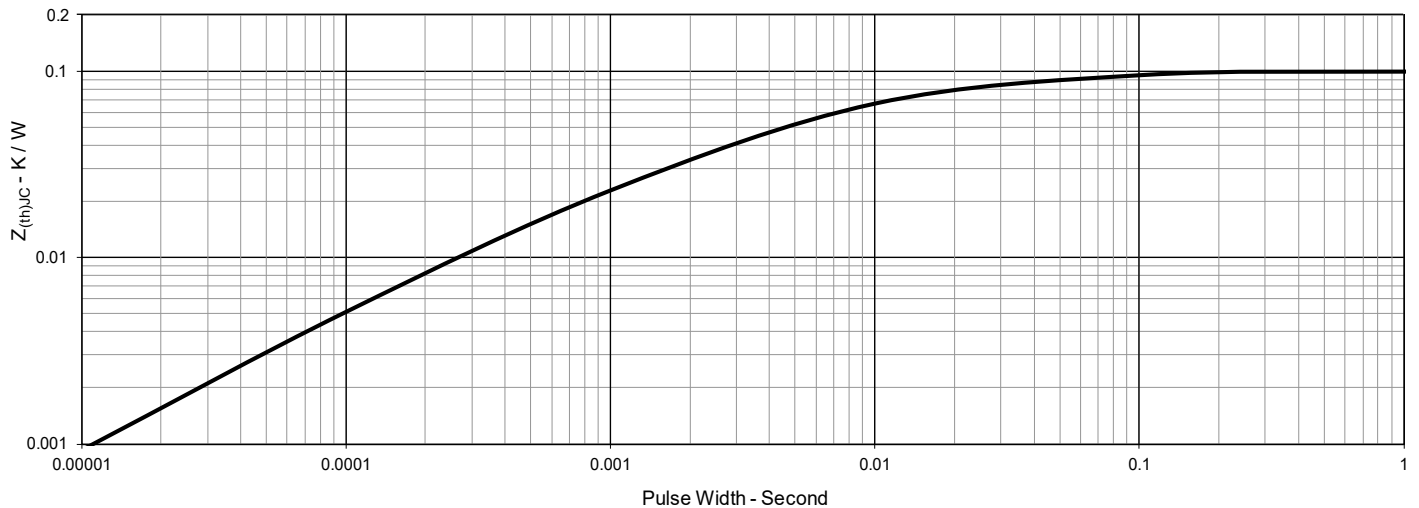


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

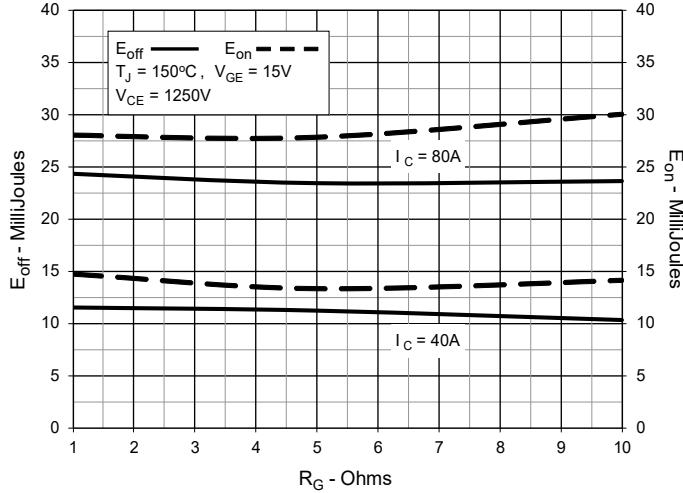


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

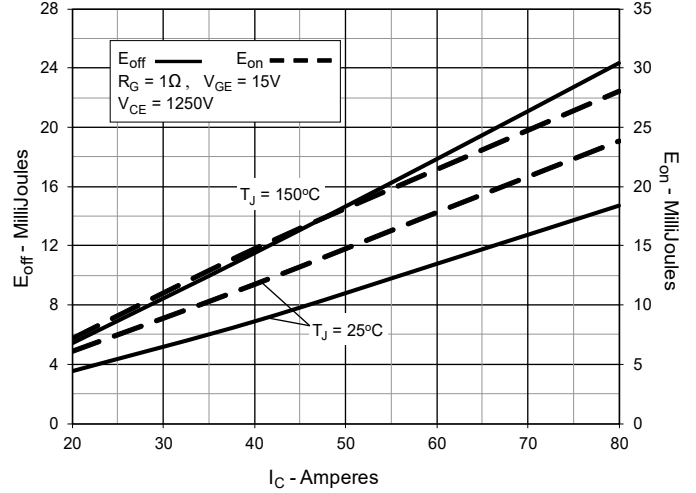


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

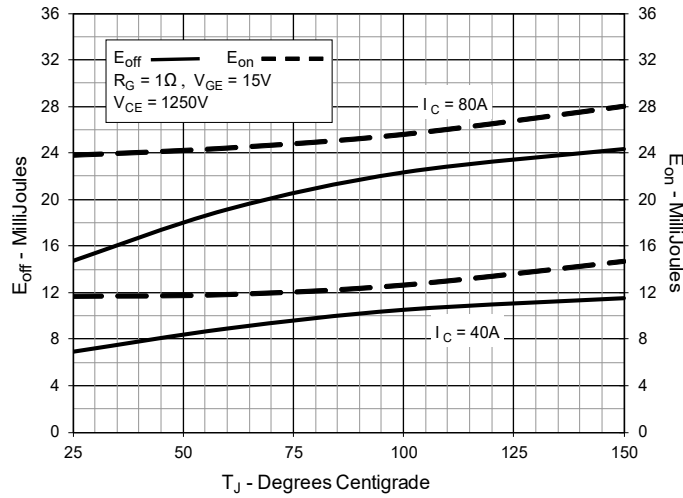


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

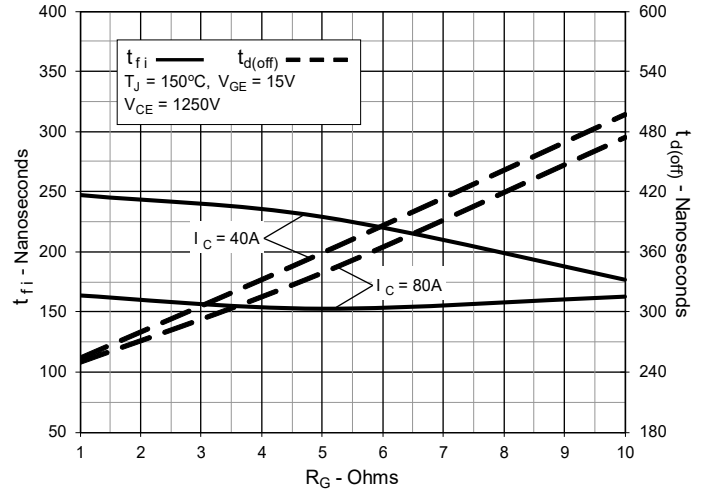


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

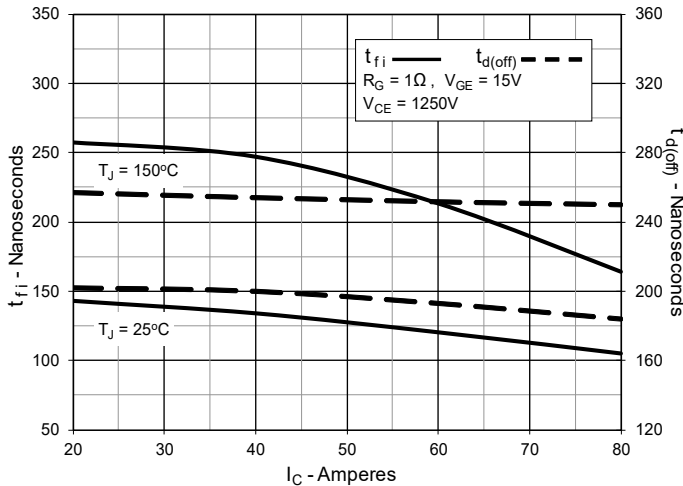


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

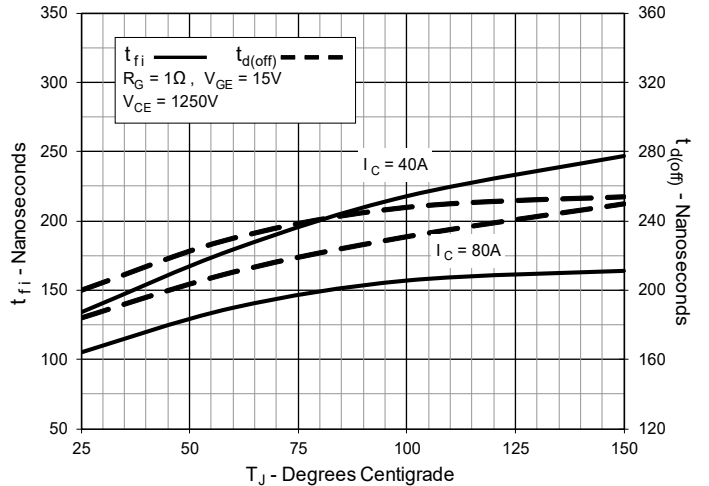


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

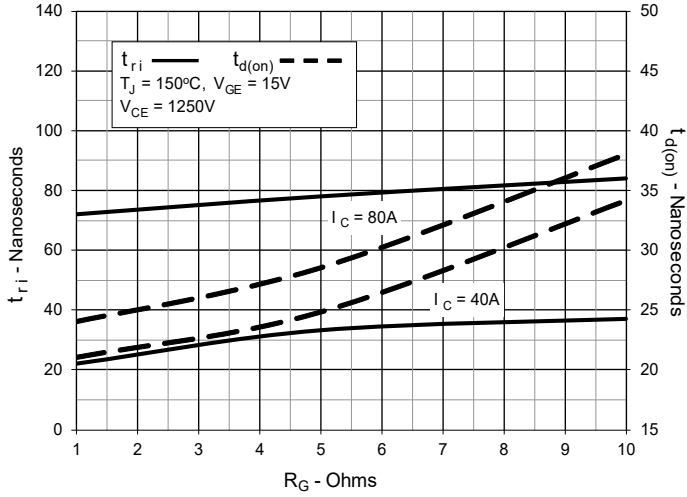


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

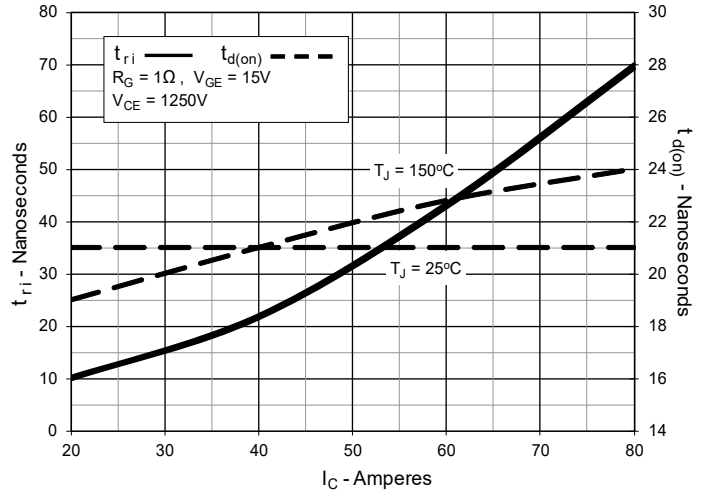
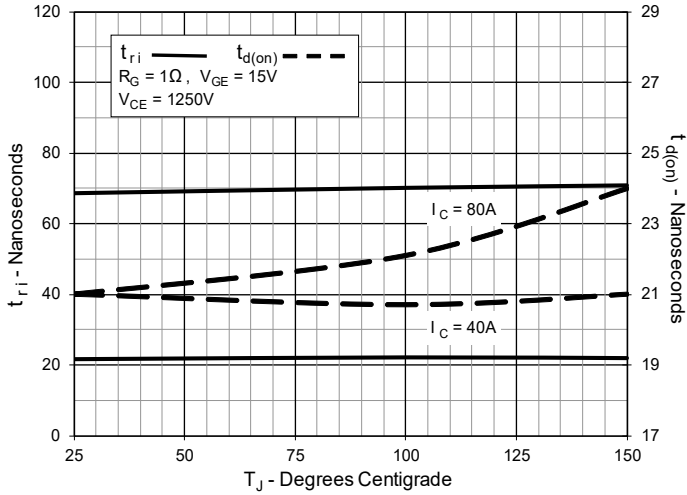
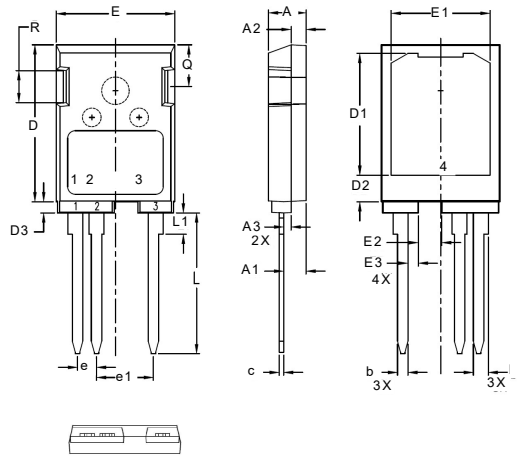


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature



TO-247PLUS-HV Outline


1 - Gate
2,4 - Emitter
3 - Collector

SYM	Inches		Millimeters	
	MIN	MAX	MIN	MAX
A	0.193	0.201	4.90	5.10
A1	0.114	0.122	2.90	3.10
A2	0.075	0.083	1.90	2.10
A3	0.035	0.043	0.90	1.10
b	0.053	0.059	1.35	1.50
b1	0.075	0.083	1.90	2.10
c	0.022	0.030	0.55	0.75
D	0.819	0.843	20.8	21.4
D1	0.638	0.646	16.2	16.4
D2	0.134	0.146	3.40	3.70
D3	0.055	0.063	1.40	1.60
E	0.622	0.638	15.8	16.2
E1	0.520	0.528	13.2	13.4
E2	0.118	0.126	3.00	3.20
E3	0.051	0.059	1.30	1.50
e	0.100	BSC	2.54	BSC
e1	0.300	BSC	7.62	BSC
L	0.732	0.748	18.60	19.0
L1	0.106	0.118	2.70	3.00
Q	0.216	0.224	5.50	5.70
R	0.165	0.169	4.20	4.30